

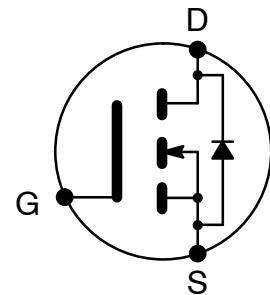


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## NTE2932 MOSFET N-Channel, Enhancement Mode High Speed Switch TO3PML Type Package

**Features:**

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower  $R_{DS(on)}$ :  $0.071 \leq$  Typ
- Lower Leakage Current:  $10^\circ$  A (Max) @  $V_{DS} = 200V$



**Absolute Maximum Ratings:**

Drain-to-Source Voltage, $V_{DSS}$ .....	200V
Drain Current, $I_D$	
Continuous	
$T_C = +25^\circ C$ .....	21.3A
$T_C = +100^\circ C$ .....	13.5A
Pulsed (Note 1) .....	130A
Total Power Dissipation ( $T_C = +25^\circ C$ ), $P_D$ .....	90W
Derate Above $25^\circ C$ .....	0.72W/ $^\circ C$
Gate-Source Voltage, $V_{GS}$ .....	$\pm 30V$
Single Pulsed Avalanche Energy (Note 2), $E_{AS}$ .....	605mJ
Avalanche Current (Note 1), $I_{AR}$ .....	21.3A
Repetitive Avalanche Energy (Note 1), $E_{AR}$ .....	9mJ
Peak Diode Recovery $dv/dt$ (Note 3), $dv/dt$ .....	5.0V/ns
Operating Junction Temperature Range, $T_J$ .....	$-55^\circ$ to $+150^\circ C$
Storage Temperature Range, $T_{stg}$ .....	$-55^\circ$ to $+150^\circ C$
Maximum Lead Temperature (During Soldering, 1/8" from case, 5sec), $T_L$ .....	$+300^\circ C$
Thermal Resistance, Junction-to-Case, $R_{thJC}$ .....	1.38 $^\circ C/W$
Thermal Resistance, Junction-to-Ambient, $R_{thJA}$ .....	40 $^\circ C/W$

Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 2.  $L = 2mH$ ,  $I_{AS} = 21.3A$ ,  $V_{DD} = 50V$ ,  $R_G = 27\leq$ , Starting  $T_J = +25^\circ C$ .

Note 3.  $I_{SD} \leq 32A$ ,  $di/dt \leq 320A/^\circ s$ ,  $V_{DD} \leq V_{(BR)DSS}$ , Starting  $T_J = +25^\circ C$ .

**Electrical Characteristics:** ( $T_C = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain–Source Breakdown Voltage	$BV_{DSS}$	$V_{GS} = 0V, I_D = 250^\circ A$	200	–	–	V
Breakdown Voltage Temperature Coefficient	$\pm V_{(BR)DSS} / \pm T_J$	$I_D = 250^\circ A$	–	0.24	–	V/ $^\circ\text{C}$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = 5V, I_D = 250^\circ A$	2.0	–	4.0	V
Gate–Source Leakage Forward	$I_{GSS}$	$V_{GS} = 30V$	–	–	100	nA
Gate–Source Leakage Reverse	$I_{GSS}$	$V_{GS} = -30V$	–	–	-100	nA
Drain–to–Source Leakage Current	$I_{DSS}$	$V_{DS} = 200V$	–	–	10	$^\circ A$
		$V_{DS} = 160V, T_C = +150^\circ\text{C}$	–	–	100	$^\circ A$
Static Drain–Source ON Resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10.65A, \text{Note 4}$	–	–	0.085	$\leq$
Forward Transconductance	$g_{fs}$	$V_{DS} = 40V, I_D = 10.65A, \text{Note 4}$	–	16.64	–	mhos
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = 25V, f = 1\text{MHz}$	–	2300	3000	pF
Output Capacitance	$C_{oss}$		–	410	475	pF
Reverse Transfer Capacitance	$C_{rss}$		–	200	230	pF
Turn–On Delay Time	$t_{d(on)}$	$V_{DD} = 100V, I_D = 32A, R_G = 6.2\leq, \text{Note 4, Note 5}$	–	21	50	ns
Rise Time	$t_r$		–	20	50	ns
Turn–Off Delay Time	$t_{d(off)}$		–	77	160	ns
Fall Time	$t_f$		–	38	90	ns
Total Gate Charge	$Q_g$	$V_{GS} = 10V, I_D = 32A, V_{DS} = 160V, \text{Note 4, Note 5}$	–	95	123	nC
Gate–Source Charge	$Q_{gs}$		–	18	–	nC
Gate–Drain (“Miller”) Charge	$Q_{gd}$		–	45.3	–	nC
<b>Source–Drain Diode Ratings and Characteristics</b>						
Continuous Source Current	$I_S$	(Body Diode)	–	–	21.3	A
Pulse Source Current	$I_{SM}$	(Body Diode) Note 1	–	–	130	A
Diode Forward Voltage	$V_{SD}$	$T_J = +25^\circ\text{C}, I_S = 21.3A, V_{GS} = 0V, \text{Note 4}$	–	–	1.5	V
Reverse Recovery Time	$t_{rr}$	$T_J = +25^\circ\text{C}, I_F = 32A, di_F/dt = 100A/^\circ\text{s}, \text{Note 4}$	–	203	–	ns
Reverse Recovery Charge	$Q_{rr}$		–	1.52	–	$^\circ\text{C}$

Note 1. Repetitive Rating: Pulse width limited by maximum junction temperature.

Note 4. Pulse Test: Pulse Width = 250 $^\circ$  s, Duty Cycle  $\leq$  2%.

Note 5. Essentially independent of operating temperature.

